

In the Abstract:

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The present invention discloses methods for manufacturing a metal line of a semiconductor device that can prevent undesirable etching of an edge of an interlayer insulating film. In accordance with the method, a lower metal line exposed by a via contact hole is covered by a photoresist film pattern which is formed via an exposure and development process using an upper metal line mask. An etching process is performed using the photoresist film pattern as a mask to form the upper metal line region that is then filled to form an upper metal line after removing the photoresist film pattern.